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deuterium, mos, annealing Refine

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CNF	TOC	PDF	**Multi-level metal CMOS manufacturing with deuterium for improved hot carrier reliability** *Kizilyalli, I.C.; Weber, G.; Chen, Z.; Abeln, G.; Schonfield, M.; Kotzias, B.; Register, F.; Harris, E.; Sen, S.; Chetlur, S.; Patel, M.; Stirling, L.; Huang, R.; Massengale, A.; Roy, P.K.; Higashi, G.; Foley, E.; Lee, J.; Lyding, J.; Hess, K.* Electron Devices Meeting, 1998. IEDM '98 Technical Digest., International , 1998 , Page(s): 935 -938
PER	TOC	PDF	**The time-dependence of post-irradiation interface trap build-up in deuterium-annealed oxides (n-MOSFET)** *Saks, N.S.; Rendell, R.W.* applicant submitted Nuclear Science, IEEE Transactions on Volume: 39 6 1-2 , Dec. 1992 , Page(s): 2220 -2229
PER	TOC	PDF	**Effects of minute impurities (H, OH, F) on SiO/sub 2//Si interface as investigated by nuclear resonant reaction and electron spin resonance** *Ohji, Y.; Nishioka, Y.; Yokogawa, K.; Mukai, K.; Qiu, Q.; Arai, E.; Sugano, T.* Electron Devices, IEEE Transactions on Volume: 37 7 , July 1990 , Page(s): 1635 -1642
PER	TOC	PDF	**Giant isotope effect in hot electron degradation of metal oxide silicon devices** *Hess, K.; Kizilyalli, I.C.; Lyding, J.W.* Electron Devices, IEEE Transactions on Volume: 45 2 , Feb. 1998 , Page(s): 406 -416
PER	TOC	PDF	**1/f noise and radiation effects in MOS devices** *Fleetwood, D.M.; Meisenheimer, T.L.; Scofield, J.H.*

Electron Devices, IEEE Transactions on
Volume: 41 11 , Nov. 1994 , Page(s): 1953 -1964

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Residual charges effect on the annealing behavior of Co-60 irradiated MOS capacitors

Hwu, J.-G.; Lee, G.-S.; Lee, S.-C.; Wang, W.-S.

Nuclear Science, IEEE Transactions on
Volume: 35 1 1-2 , Feb. 1988 , Page(s): 960 -965

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The nature of the trapped hole annealing process

Lelis, A.J.; Oldham, T.R.; Boesch, H.E., Jr.; McLean, F.B.

Nuclear Science, IEEE Transactions on
Volume: 36 6 1-2 , Dec. 1989 , Page(s): 1808 -1815

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Degradation of the characteristics of p/sup +/ poly MOS capacitors with NO nitrided gate oxide due to post nitrogen annealing

Mazumder, M.K.; Teramoto, A.; Kobayashi, K.; Sekine, M.; Kawazu, S.; Koyama, H.

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Effect of N/sub 2/O or NO annealing of wet oxide at different times on TDDB characteristics

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Clark, W.F.; Ference, T.G.; Hook, T.B.; Watson, K.M.; Mittl, S.W.; Burnham, J.S.

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Volume: 20 1 , Jan. 1999 , Page(s): 48 -50

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A comparative study of hydrogen and deuterium plasma treatment effects on the performance and reliability of polysilicon TFTs

Tung, Y.-J.; Boyce, J.; Ho, J.; Haung, X.; King, T.-J.

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Volume: 37 6 2 , Dec. 1990 , Page(s): 1806 -1817

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Ryu, B.H.; Kwon, S.S.; Lim, K.J.; Park, S.G.; Kim, B.H.; Kim, H.H.

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The annealing behavior of oxide trapped charges and interface traps in fluorinated NMOSFETS

Guoqiang Zhang; Rongliang Yan; Diyuan Ren

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Volume: 1 , 1995 , Page(s): 269 -272 vol.1

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Ultradry annealing after polysilicon electrode formation for improving the TDDB lifetime of ultrathin silicon oxide films in MOS diodes

Yamada, H.; Abe, M.

IEEE Electron Device Letters
Volume: 12 10 , Oct. 1991 , Page(s): 536 -538

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Dose rate and annealing effects on total dose response of MOS and bipolar circuits

Carriere, T.; Beaucour, J.; Gach, A.; Johlander, B.; Adams, L.

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Volume: 42 6 1 , Dec. 1995 , Page(s): 1567 -1574

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A bias voltage dependence of trapped hole annealing and its measurement technique (MOS capacitor)

Kuboyama, S.; Goka, T.; Tamura, T.

Nuclear Science, IEEE Transactions on
Volume: 38 6 1 , Dec. 1991 , Page(s): 1140 -1144

PER

Deuterium post-metal annealing of MOSFET's for improved hot carrier reliability

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Volume: 18 3 , March 1997 , Page(s): 81 -83

CNF

Generations of interface states in electrically stressed and high temperature annealed MOS devices

Berger, M.; Shappir, L.

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Kato, M.; Watanabe, K.; Okabe, T.

Nuclear Science, IEEE Transactions on
Volume: 38 6 1 , Dec. 1991 , Page(s): 1094 -1100

CNF

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Radiation and its Effects on Devices and Systems, 1991. RADECS 91., First European Conference on , 1992 , Page(s): 362 -367

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The properties and annealing of gate oxide damage of oxynitride-passivated CMOS transistors arising from mechanical stresses during packaging

Doyle, B.; Lau, D.

Electron Devices Meeting, 1989. Technical Digest., International , 1989 , Page(s): 91 -94

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High quality SiO/sub 2//Si interfaces of poly-crystalline silicon thin film transistors by annealing in wet atmosphere

Sano, N.; Sekiya, M.; Hara, M.; Kohno, A.; Sameshima, T.

IEEE Electron Device Letters

Volume: 16 5 , May 1995 , Page(s): 157 -160

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PER			**Parametric yield optimisation of MOS VLSI circuits based on simulated annealing and its parallel implementation** *Conti, M.; Orcioni, S.; Turchetti, C.* Circuits, Devices and Systems, IEE Proceedings- Volume: 141 5 , Oct. 1994 , Page(s): 387 -398
PER			**Effects of irradiation temperature on MOS radiation response** *Shaneyfelt, M.R.; Schwank, J.R.; Fleetwood, D.M.; Winokur, P.S.* Nuclear Science, IEEE Transactions on Volume: 45 3 3 , June 1998 , Page(s): 1372 -1378
PER			**The role of border traps in MOS high-temperature postirradiation annealing response** *Fleetwood, D.M.; Shaneyfelt, M.R.; Riewe, L.C.; Winokur, P.S.; Reber, R.A., Jr.* Nuclear Science, IEEE Transactions on Volume: 40 6 1-2 , Dec. 1993 , Page(s): 1323 -1334
PER			**Reduction of oxide charge and interface-trap density in MOS capacitors with ITO gates** *Weijtens, C.H.L.* Electron Devices, IEEE Transactions on Volume: 39 8 , Aug. 1992 , Page(s): 1889 -1894
PER			**Leakage current reduction in chemical-vapor-deposited Ta/sub 2/O/sub 5/ films by rapid thermal annealing in N/sub 2/O** *Sun, S.C.; Chen, T.F.* IEEE Electron Device Letters Volume: 17 7 , July 1996 , Page(s): 355 -357
PER			**Effects of post-stress hydrogen annealing on MOS oxides after /sup 60/Co irradiation or Fowler-Nordheim injection** *Saks, N.S.; Klein, R.B.; Stahlbush, R.E.; Mrstik, B.J.; Rendell, R.W.* Nuclear Science, IEEE Transactions on Volume: 40 6 1-2 , Dec. 1993 , Page(s): 1341 -1349
PER			**Thermal stability of deuterium in InAlN and InAlGaN** *Pearton, S.J.; Abernathy, C.R.; MacKenzie, J.D.; Wilson, R.G.; Ren,*

F.; Zavada, J.M.
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Volume: 31 4 , 16 Feb. 1995 , Page(s): 327 -329

PER **Re-evaluation of the benefits of postoxidation annealing on sub-100 /spl Aring/ gate oxide quality**
Ajuria, S.A.; Maiti, B.; Tobin, P.J.; Mele, T.C.
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Volume: 17 6 , June 1996 , Page(s): 282 -284

PER **Fast switched-bias annealing of radiation-induced oxide-trapped charge and its application for testing of radiation effects in MOS structures**
Pershenkov, V.S.; Belyakov, V.V.; Shalnov, A.V.
Nuclear Science, IEEE Transactions on
Volume: 41 6 1 , Dec. 1994 , Page(s): 2593 -2599

PER **Effect of rapid thermal reoxidation on the electrical properties of rapid thermally nitrided thin-gate oxides**
Joshi, A.B.; Lo, G.O.; Shih, D.K.; Kwong, D.-L.
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Volume: 39 4 , April 1992 , Page(s): 883 -892

CNF **The effects of hydrogen and deuterium incorporation on the electrical performance of a GaAs MESFET**
Eng, D.C.; Culbertson, R.J.; MacWilliams, K.P.
Gallium Arsenide Integrated Circuit (GaAs IC) Symposium, 1995. Technical Digest 1995., 17th Annual IEEE , 1995 , Page(s): 140 -143

CNF **Process-induced damage-a study of hydrogen and deuterium passivation**
Rangan, S.; Krishnan, S.; Ashok, S.
Plasma Process-Induced Damage, 1998 3rd International Symposium on , 1998 , Page(s): 213 -216

CNF **Investigation of tunneling current through thin dielectrics**
Evtukh, A.A.; Litovchenko, V.G.; Kizijak, A.Yu.
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CNF **Effects of irradiation temperature on MOS radiation response**
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CNF **On aspects of radiation damage in Tokamak diagnostics**
DelMedico, S.; Barnouin, O.; Petra, M.; Miley, G.H.
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Lai, K.; Kumar, K.; Chou, A.; Lee, J.C.
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Volume: 17 3 , March 1996 , Page(s): 82 -84

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Effects of nitric oxide annealing of thermally grown silicon dioxide characteristics

Yao, Z.-Q.; Harrison, H.B.; Dimitrijev, S.; Yeow, Y.T.

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Volume: 16 8 , Aug. 1995 , Page(s): 345 -347

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Effects of interface traps and border traps on MOS postirradiation annealing response

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Volume: 42 6 1 , Dec. 1995 , Page(s): 1698 -1707

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Effects of wet oxidation/anneal on interface properties of thermally oxidized SiO/sub 2//SiC MOS system and MOSFET's

Yano, H.; Katafuchi, F.; Kimoto, T.; Matsunami, H.

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Comparison of the generation of interface states in MOS structures due to /sup 60/Co and VUV irradiation accompanied with photoinjection of electrons

Scharf, S.; Schmidt, M.; Wulf, F.; Braunig, D.

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Volume: 41 3 1-2 , June 1994 , Page(s): 460 -465

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Three-point method of prediction of MOS device response in space environments

Pershenkov, V.S.; Belyakov, V.V.; Cherepko, S.V.; Shvetzov-Shilovsky, I.N.

Nuclear Science, IEEE Transactions on

Volume: 40 6 1-2 , Dec. 1993 , Page(s): 1714 -1720

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1/f noise in n- and p-channel MOS devices through irradiation and annealing

Meisenheimer, T.L.; Fleetwood, D.M.; Shaneyfelt, M.R.; Riewe, L.C.

Nuclear Science, IEEE Transactions on

Volume: 38 6 1 , Dec. 1991 , Page(s): 1297 -1303

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Radiation hardened micron and submicron MOSFETs containing fluorinated oxides

Nishioka, Y.; Ohyu, K.; Ohji, Y.; Kato, M.; da Silva, E.F., Jr.; Ma, T.P.

Nuclear Science, IEEE Transactions on

Volume: 36 6 1-2 , Dec. 1989 , Page(s): 2116 -2123

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Effects of N distribution on charge trapping and TDDB characteristics of N/sub 2/O annealed wet oxide

Mazumder, M.K.; Teramoto, A.; Komori, J.; Sekine, M.; Kawazu, S.; Mashiko, Y.

Electron Devices, IEEE Transactions on

Volume: 46 6 , June 1999 , Page(s): 1121 -1126

PER

Low-temperature furnace-grown reoxidized nitrided oxide gate dielectrics as a barrier to boron penetration

Fang, H.; Krisch, K.S.; Gross, B.J.; Sodini, C.G.; Chung, J.;

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JPAB	deuterium, MOS	47461	L3
JPAB	deuterium, semiconductor, annealing or heat?	306156	L2
JPAB	deuterium, semiconductor	284136	L1

Document Number 18

PAT-NO: JP411087712A
DOCUMENT-IDENTIFIER: JP 11087712 A
TITLE: DEUTERIUM SUBSTANCE FOR USE IN SEMICONDUCTOR TREATMENT

PUBN-DATE: March 30, 1999

INVENTOR-INFORMATION:
NAME
CLARK, WILLIAM F
FERENCE, THOMAS G
HOOK, TERENCE B
MARTIN, DALE W

ASSIGNEE-INFORMATION:
NAME COUNTRY
INTERNATL BUSINESS MACH CORP N/A

APPL-NO: JP10192725
APPL-DATE: July 8, 1998

INT-CL (IPC): H01 L 29/78; H01 L 21/324

ABSTRACT:
PROBLEM TO BE SOLVED: To ensure strong resistance against hot electron effect on the interface of silicon/silicon dioxide while suppressing damage of an element by substituting deuterium for hydrogen of a film formation reactive substance being used in production of semiconductor thereby producing a deuterium film substance at the time of film formation.

SOLUTION: A MOSFET element 100 comprises a single crystal silicon substrate 11, source-drain regions 12, 13, a gate oxide 14, a gate polysilicon 15, a gate sidewall spacer 16, a silicon nitride barrier wall 18, a passive oxide layer (e.g. SiO2) to be bonded, and a self-aligned silicate layer 17. These components of gate oxide 14, polysilicon 15, or the like, in the element contain hydrogen molecules emitted into the oxide during annealing process. The hydrogen atom is substituted by deuterium at the time of film formation to produce a deuterium film substance. Hydrogen migrates to the interface of silicon/silicon dioxide of these component of element to produce a deuterium substance thus exhibiting resistance against heat cycle.

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TITLE: MOS SEMICONDUCTOR INTEGRATED CIRCUIT

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TITLE: TEMPERATURE COMPENSATING CRYSTAL OSCILLATOR

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☐ 13. Document ID: JP 11087750 A

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TITLE: MANUFACTURE OF IMPURITY SEMICONDUCTOR, P-TYPE SEMICONDUCTOR, N-TYPE SEMICONDUCTOR, AND SEMICONDUCTOR DEVICE

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Entry 14 of 66791 File: JPAB Mar 30, 19

PUB-NO: JP411087735A
DOCUMENT-IDENTIFIER: JP 11087735 A
TITLE: SEMICONDUCTOR DEVICE AND ITS MANUFACTURE

Full | Title | Citation | Front | Review | Classification | Date | Reference | Claims | KWIC | Clip Img | Image

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PUB-NO: JP411087730A
DOCUMENT-IDENTIFIER: JP 11087730 A
TITLE: POLYCRYSTALLINE SEMICONDUCTOR THIN FILM, ITS FORMATION METHOD, POLYCRYSTALLINE SEMICONDUCTOR TFT AND TFT SUBSTRATE

Full | Title | Citation | Front | Review | Classification | Date | Reference | Claims | KWIC | Clip Img | Image

☐ 16. Document ID: JP 11087727 A

Entry 16 of 66791 File: JPAB Mar 30, 19

PUB-NO: JP411087727A
DOCUMENT-IDENTIFIER: JP 11087727 A
TITLE: SEMICONDUCTOR DEVICE

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☐ 17. Document ID: JP 11087720 A

Entry 17 of 66791 File: JPAB Mar 30, 19

PUB-NO: JP411087720A
DOCUMENT-IDENTIFIER: JP 11087720 A
TITLE: SEMICONDUCTOR DEVICE AND LIQUID CRYSTAL DISPLAY DEVICE

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TITLE: DEUTERIUM SUBSTANCE FOR USE IN SEMICONDUCTOR TREATMENT

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TITLE: FABRICATION OF TRANSISTOR

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TITLE: PRODUCTION OF PHOTOCATALYST THIN FILM SUPPORTING NOBLE METAL FINE PARTICLE

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PUB-NO: JP411070190A
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☐ 193. Document ID: JP 11069976 A

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PUB-NO: JP411069976A
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TITLE: COMPOSITION FOR TREATMENT OF MALIGNANT TUMOR

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☐ 194. Document ID: JP 11069817 A

Entry 194 of 66791 File: JPAB Mar 9, 199

PUB-NO: JP411069817A
DOCUMENT-IDENTIFIER: JP 11069817 A
TITLE: SWITCHING ELEMENT DRIVER FOR DRIVE OF TRANSFORMER

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☐ 195. Document ID: JP 11069611 A

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PUB-NO: JP411069611A
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TITLE: ELECTRICALLY-DRIVEN MOTOR DRIVE-TYPE STEERING APPARATUS

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☐ 196. Document ID: JP 11068938 A

Entry 196 of 66791 File: JPAB Mar 9, 199

PUB-NO: JP411068938A
DOCUMENT-IDENTIFIER: JP 11068938 A
TITLE: TMN AGENT GENERATING SYSTEM

Full | Title | Citation | Front | Review | Classification | Date | Reference | Claims | KWIC | Clip Img | Image

☐ 197. Document ID: JP 11068695 A

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PUB-NO: JP411068695A
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TITLE: IN-PHASE/ORTHOGONAL FRAME ALTERNATE ARRANGEMENT TYPE DATA COMMUNICATION SYSTEM

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PUB-NO: JP411068560A
DOCUMENT-IDENTIFIER: JP 11068560 A
TITLE: PLL FREQUENCY SYNTHESIZER AND CHARGE PUMP CIRCUIT

Full | Title | Citation | Front | Review | Classification | Date | Reference | Claims | KWIC | Clip Img | Image

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Entry 199 of 66791 File: JPAB Mar 9, 199

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TITLE: COUNTER AND PLL CIRCUIT

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JPAB	deuterium, MOS	47461	L3
JPAB	deuterium, semiconductor, annealing or heat?	306156	L2
JPAB	deuterium, semiconductor	284136	L1

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371. Document ID: US 5606265 A

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PAT-NO: US005606265A
DOCUMENT-IDENTIFIER: US 5606265 A
TITLE: Semiconductor integrated circuits with power reduction mechanism

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372. Document ID: US 5606197 A

Entry 372 of 131285 File: EPAB Feb 25, 19

PAT-NO: US005606197A
DOCUMENT-IDENTIFIER: US 5606197 A
TITLE: High capacitance capacitor in an integrated function block or an integrated circuit

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373. Document ID: US 5605086 A

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PAT-NO: US005605086A
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TITLE: Compound mitre saw

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374. Document ID: WO 9706564 A1

Entry 374 of 131285 File: EPAB Feb 20, 19

PAT-NO: WO009706564A1

DOCUMENT-IDENTIFIER: WO 9706564 A1
TITLE: SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE SAME

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375. Document ID: DE 19530518 A1
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TITLE: Metal carbonitride hard coating

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376. Document ID: DE 19530517 A1
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PAT-NO: DE019530517A1
DOCUMENT-IDENTIFIER: DE 19530517 A1
TITLE: Metal carbonitride hard coating

Full | Title | Citation | Front | Review | Classification | Date | Reference | Claims | KWIC | Image

377. Document ID: DE 19530454 A1
Entry 377 of 131285 File: EPAB Feb 20, 19

PAT-NO: DE019530454A1
DOCUMENT-IDENTIFIER: DE 19530454 A1
TITLE: Economical continuous oxidative dehydrogenation of propane to propene in high yield

Full | Title | Citation | Front | Review | Classification | Date | Reference | Claims | KWIC | Image

378. Document ID: EP 758684 A1
Entry 378 of 131285 File: EPAB Feb 19, 19

PAT-NO: EP000758684A1
DOCUMENT-IDENTIFIER: EP 758684 A1
TITLE: Nickel-based superalloys with good stability at high temperatures

Full | Title | Citation | Front | Review | Classification | Date | Reference | Claims | KWIC | Image

379. Document ID: US 5604417 A
Entry 379 of 131285 File: EPAB Feb 18, 19

PAT-NO: US005604417A
DOCUMENT-IDENTIFIER: US 5604417 A
TITLE: Semiconductor integrated circuit device

Full | Title | Citation | Front | Review | Classification | Date | Reference | Claims | KWIC | Image

380. Document ID: US 5604140 A
Entry 380 of 131285 File: EPAB Feb 18, 19

PAT-NO: US005604140A
DOCUMENT-IDENTIFIER: US 5604140 A
TITLE: Method for forming fine titanium nitride film and method for fabricating semiconductor element using the same

Full | Title | Citation | Front | Review | Classification | Date | Reference | Claims | KWIC | Image

Terms	Documents
deuterium, mos	131285

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=> s deuterium (1p)(annealing or heat?) and semiconductor

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          3511 DEUTERIUM
         33850 ANNEALING
        850865 HEAT?
           894 DEUTERIUM (1P)(ANNEALING OR HEAT? )
        166753 SEMICONDUCTOR
L3          83 DEUTERIUM (1P)(ANNEALING OR HEAT? ) AND SEMICONDUCTOR
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=> d 1-83

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